

Complementary Bias Resistor Transistors

R1 = 47 kΩ, R2 = 47 kΩ

NPN and PNP Transistors with Monolithic Bias Resistor Network

**MUN5313DW1,
NSBC144EPDXV6,
NSBC144EPDP6**

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable*
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

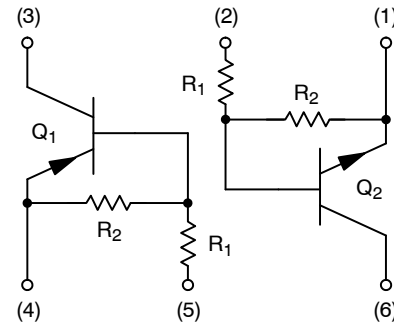
MAXIMUM RATINGS

(T_A = 25°C both polarities Q₁ (PNP) & Q₂ (NPN), unless otherwise noted)

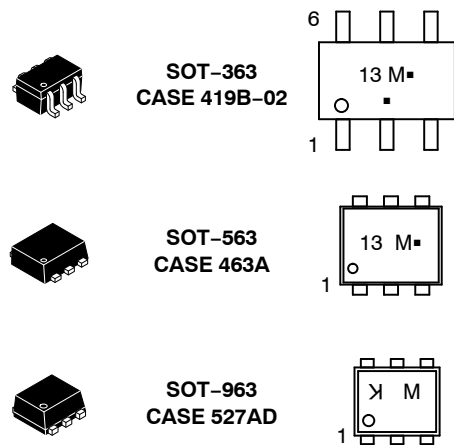
Rating	Symbol	Max	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current – Continuous	I _C	100	mAdc
Input Forward Voltage	V _{IN(fwd)}	40	Vdc
Input Reverse Voltage	V _{IN(rev)}	10	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

PIN CONNECTIONS



MARKING DIAGRAMS



13/K = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking, and shipping information on page 2 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 2.

MUN5313DW1, NSBC144EPDXV6, NSBC144EPDP6

ORDERING INFORMATION

Device	Package	Shipping†
MUN5313DW1T1G, SMUN5313DW1T1G*	SOT-363	3,000 / Tape & Reel
SMUN5313DW1T3G*	SOT-363	10,000 / Tape & Reel
NSBC144EPDXV6T1G NSVBC144EPDXV6T1G*	SOT-563	4,000 / Tape & Reel

DISCONTINUED (Note 1)

NSBC144EPDXV6T5G	SOT-563	8,000 / Tape & Reel
NSBC144EPDP6T5G	SOT-963	8,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

1. **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
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MUN5313DW1 (SOT-363) ONE JUNCTION HEATED

Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 2)	P_D	187	mW
Derate above 25°C (Note 2) (Note 3)		256	mW/ $^\circ\text{C}$
		1.5	
		2.0	
Thermal Resistance, Junction to Ambient (Note 2)	$R_{\theta JA}$	670	$^\circ\text{C}/\text{W}$
(Note 3)		490	

MUN5313DW1 (SOT-363) BOTH JUNCTION HEATED (Note 4)

Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 2)	P_D	250	mW
Derate above 25°C (Note 2) (Note 3)		385	mW/ $^\circ\text{C}$
		2.0	
		3.0	
Thermal Resistance, Junction to Ambient (Note 2)	$R_{\theta JA}$	493	$^\circ\text{C}/\text{W}$
(Note 3)		325	
Thermal Resistance, Junction to Lead (Note 2)	$R_{\theta JL}$	188	$^\circ\text{C}/\text{W}$
(Note 3)		208	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

NSBC144EPDXV6 (SOT-563) ONE JUNCTION HEATED

Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 2)	P_D	357	mW
Derate above 25°C (Note 2)		2.9	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 2)	$R_{\theta JA}$	350	$^\circ\text{C}/\text{W}$

NSBC144EPDXV6 (SOT-563) BOTH JUNCTION HEATED (Note 4)

Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 2)	P_D	500	mW
Derate above 25°C (Note 2)		4.0	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 2)	$R_{\theta JA}$	250	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

MUN5313DW1, NSBC144EPDXV6, NSBC144EPDP6

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
NSBC144EPDP6 (SOT-963) ONE JUNCTION HEATED			
Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 5)	P_D	231	MW
Derate above 25°C (Note 6)		269	mW/ $^\circ\text{C}$
		1.9	
		2.2	
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	540	$^\circ\text{C}/\text{W}$
(Note 6)		464	

NSBC144EPDP6 (SOT-963) BOTH JUNCTION HEATED (Note 4)

Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 5)	P_D	339	MW
Derate above 25°C (Note 6)		408	mW/ $^\circ\text{C}$
		2.7	
		3.3	
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	369	$^\circ\text{C}/\text{W}$
(Note 6)		306	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

- FR-4 @ Minimum Pad.
- FR-4 @ 1.0×1.0 Inch Pad.
- Both junction heated values assume total power is sum of two equally powered channels.
- FR-4 @ 100 mm^2 , 1 oz. copper traces, still air.
- FR-4 @ 500 mm^2 , 1 oz. copper traces, still air.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ both polarities Q_1 (PNP) & Q_2 (NPN), unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Base Cutoff Current ($V_{CB} = 50 \text{ V}, I_E = 0$)	I_{CBO}	-	-	100	nAdc
Collector-Emitter Cutoff Current ($V_{CE} = 50 \text{ V}, I_B = 0$)	I_{CEO}	-	-	500	nAdc
Emitter-Base Cutoff Current ($V_{EB} = 6.0 \text{ V}, I_C = 0$)	I_{EBO}	-	-	0.1	mAdc
Collector-Base Breakdown Voltage ($I_C = 10 \mu\text{A}, I_E = 0$)	$V_{(BR)CBO}$	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 7) ($I_C = 2.0 \text{ mA}, I_B = 0$)	$V_{(BR)CEO}$	50	-	-	Vdc

ON CHARACTERISTICS

DC Current Gain (Note 7) ($I_C = 5.0 \text{ mA}, V_{CE} = 10 \text{ V}$)	h_{FE}	80	140	-	
Collector-Emitter Saturation Voltage (Note 7) ($I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA}$)	$V_{CE(sat)}$	-	-	0.25	V
Input Voltage (Off) ($V_{CE} = 5.0 \text{ V}, I_C = 100 \mu\text{A}$) (NPN) ($V_{CE} = 5.0 \text{ V}, I_C = 100 \mu\text{A}$) (PNP)	$V_{i(off)}$	-	1.2	-	Vdc
		-	1.2	-	
Input Voltage (On) ($V_{CE} = 0.2 \text{ V}, I_C = 3.0 \text{ mA}$) (NPN) ($V_{CE} = 0.2 \text{ V}, I_C = 3.0 \text{ mA}$) (PNP)	$V_{i(on)}$	-	1.9	-	Vdc
		-	2.0	-	
Output Voltage (On) ($V_{CC} = 5.0 \text{ V}, V_B = 3.5 \text{ V}, R_L = 1.0 \text{ k}\Omega$)	V_{OL}	-	-	0.2	Vdc
Output Voltage (Off) ($V_{CC} = 5.0 \text{ V}, V_B = 0.5 \text{ V}, R_L = 1.0 \text{ k}\Omega$)	V_{OH}	4.9	-	-	Vdc

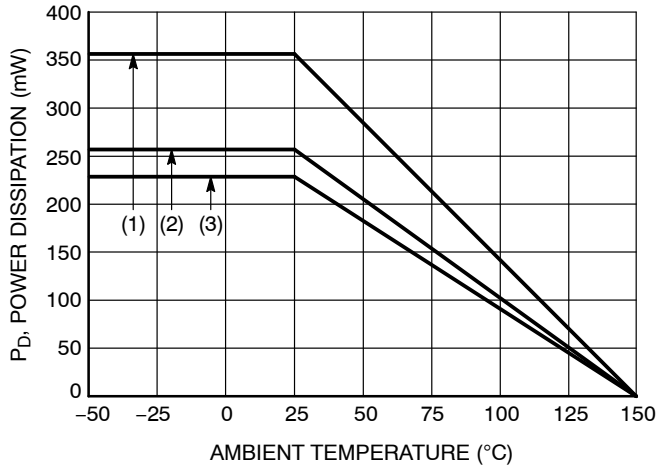
MUN5313DW1, NSBC144EPDXV6, NSBC144EPDP6

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ both polarities Q_1 (PNP) & Q_2 (NPN), unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS					
Input Resistor	R1	32.9	47	61.1	k Ω
Resistor Ratio	R_1/R_2	0.8	1.0	1.2	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

7. Pulsed Condition: Pulse Width = 300 ms, Duty Cycle \leq 2%.



- (1) SOT-363; 1.0 x 1.0 Inch Pad
- (2) SOT-563; Minimum Pad
- (3) SOT-963; 100 mm², 1 oz. Copper Trace

Figure 1. Derating Curve

TYPICAL CHARACTERISTICS – NPN TRANSISTOR
MUN5313DW1, NSBC144EPDXV6

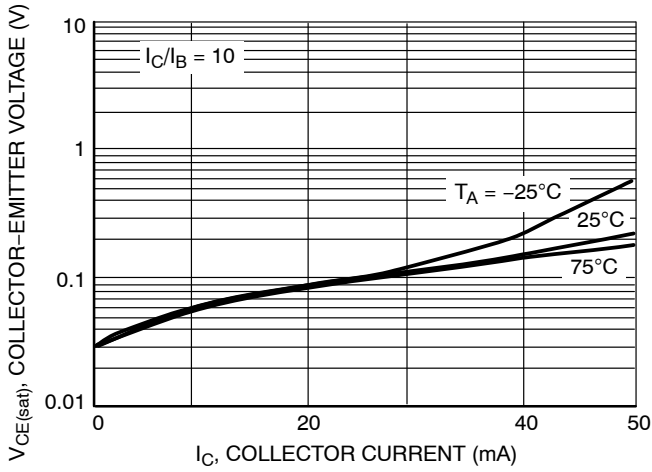


Figure 2. $V_{CE(sat)}$ vs. I_C

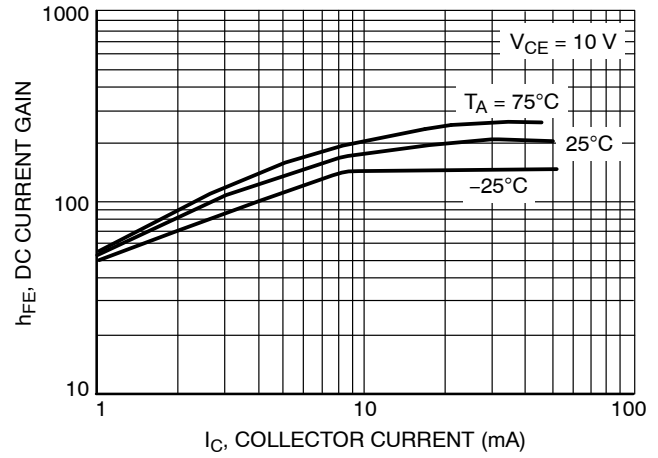


Figure 3. DC Current Gain

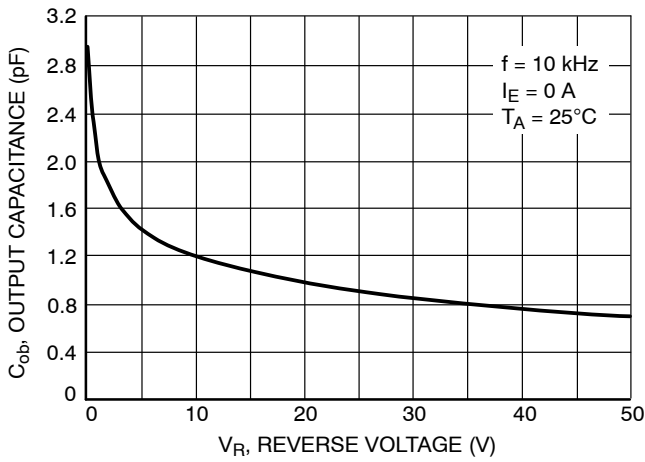


Figure 4. Output Capacitance

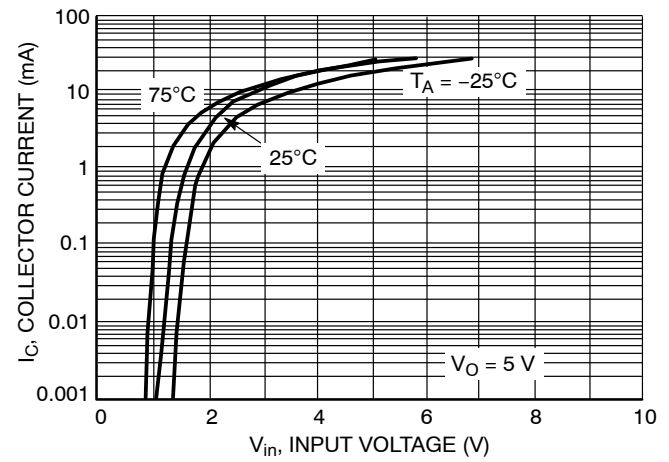


Figure 5. Output Current vs. Input Voltage

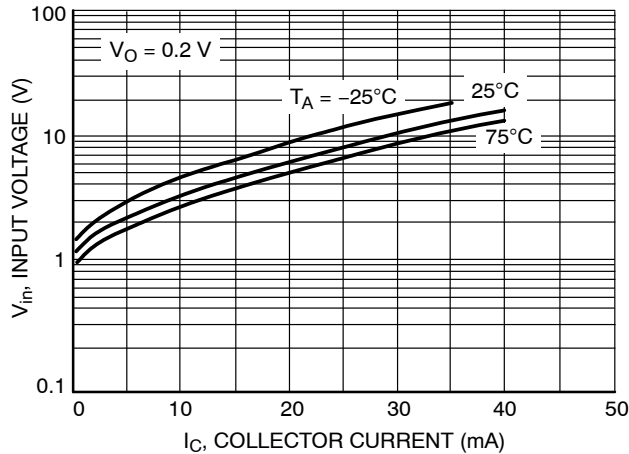


Figure 6. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS – PNP TRANSISTOR
MUN5313DW1, NSBC144EPDXV6

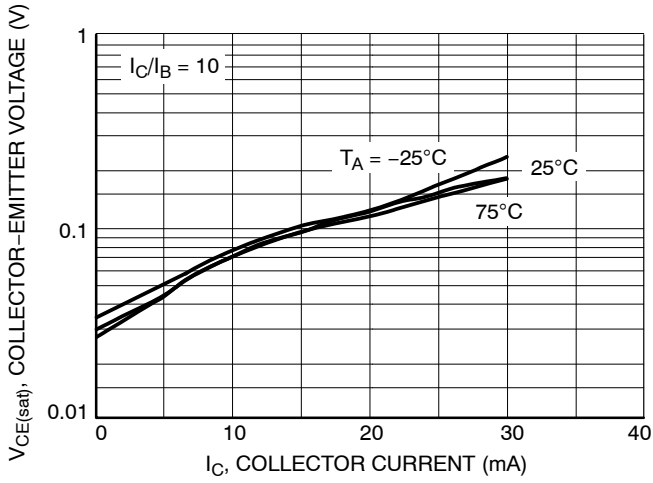


Figure 7. $V_{CE(sat)}$ vs. I_C

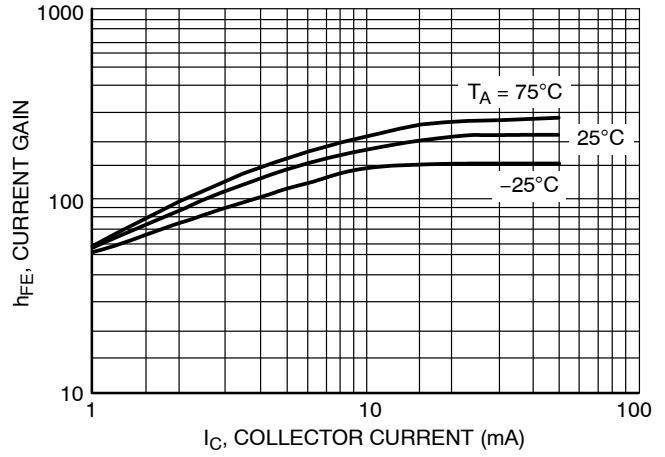


Figure 8. DC Current Gain

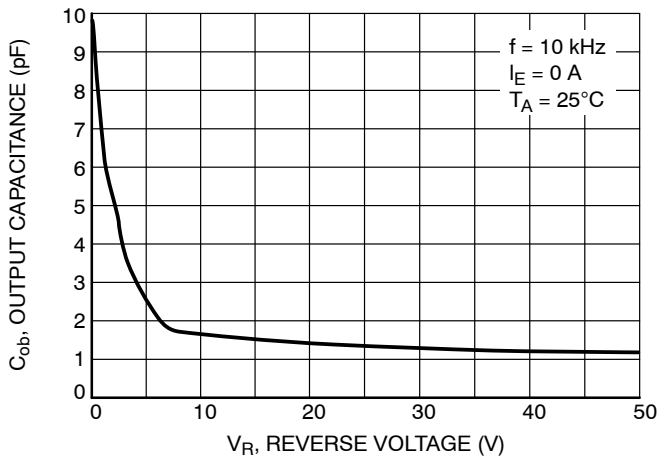


Figure 9. Output Capacitance

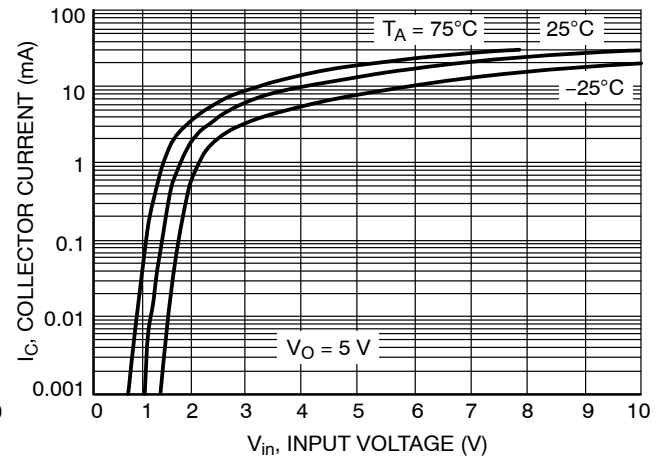


Figure 10. Output Current vs. Input Voltage

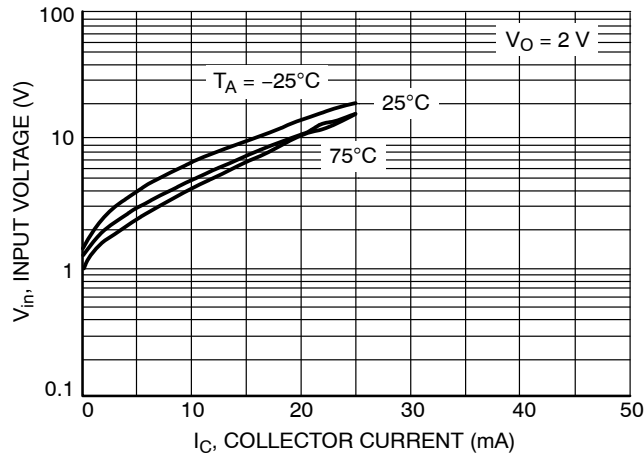


Figure 11. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS – NPN TRANSISTOR
NSBC144EPDP6

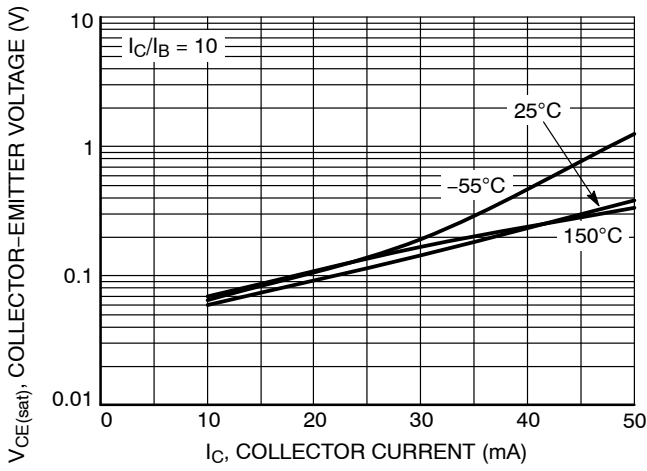


Figure 12. $V_{CE(sat)}$ vs. I_C

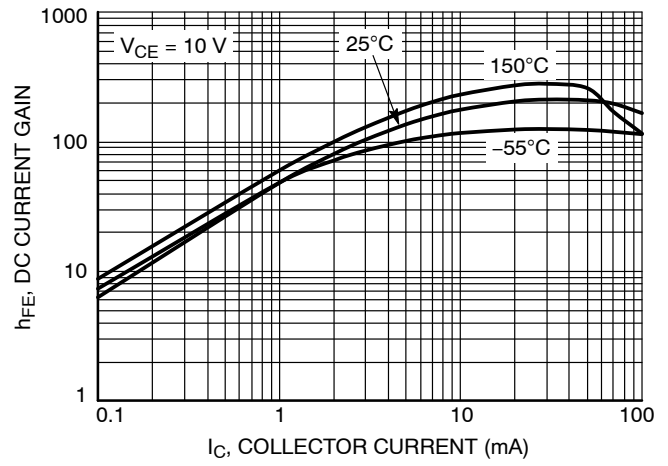


Figure 13. DC Current Gain

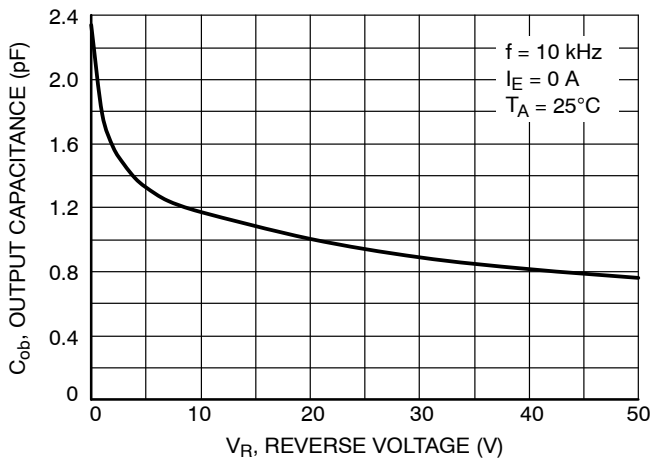


Figure 14. Output Capacitance

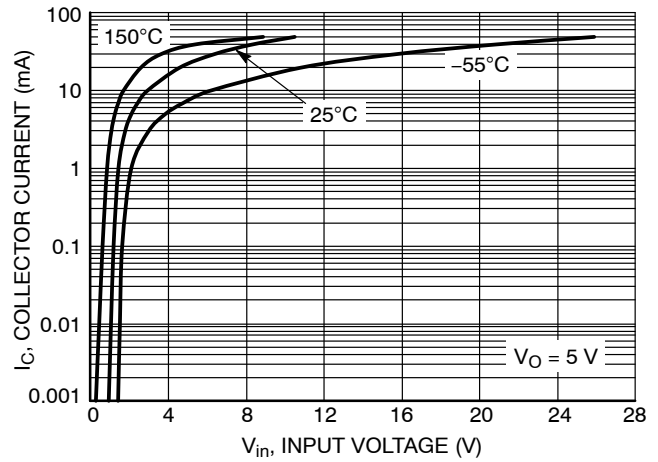


Figure 15. Output Current vs. Input Voltage

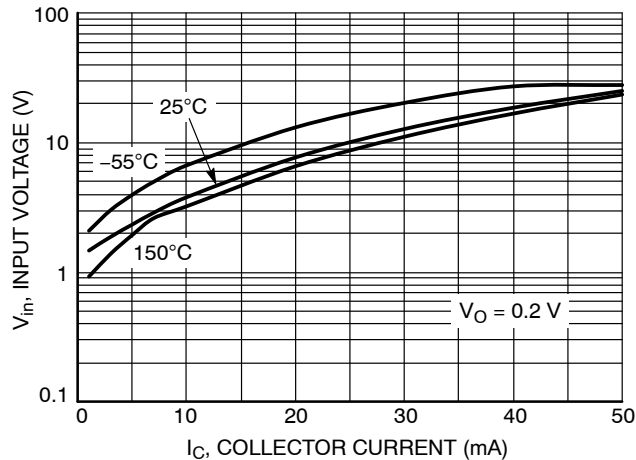


Figure 16. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS – PNP TRANSISTOR
NSBC144EPDP6

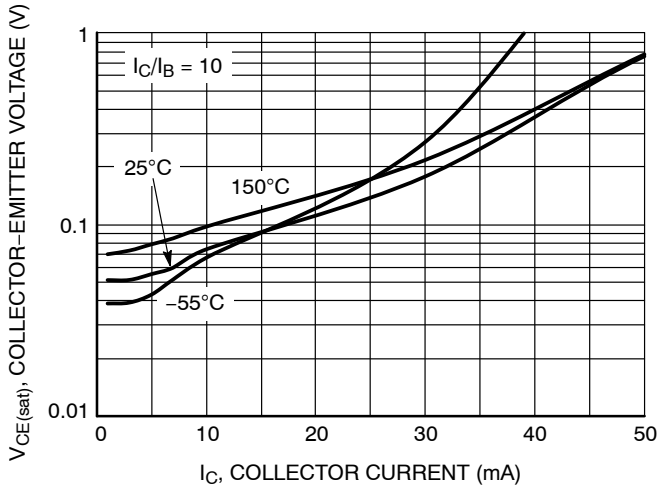


Figure 17. $V_{CE(sat)}$ vs. I_C

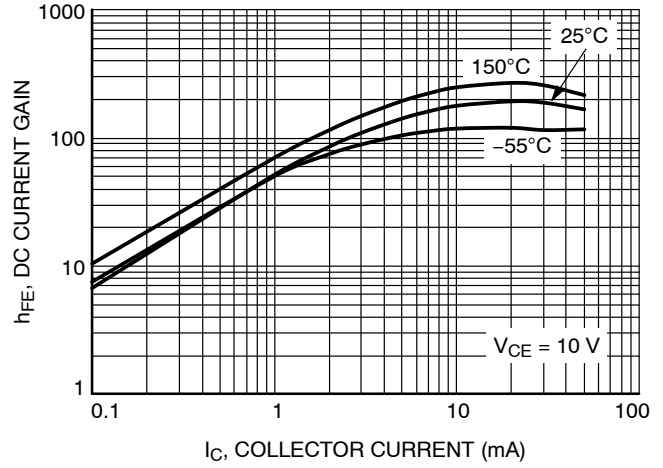


Figure 18. DC Current Gain

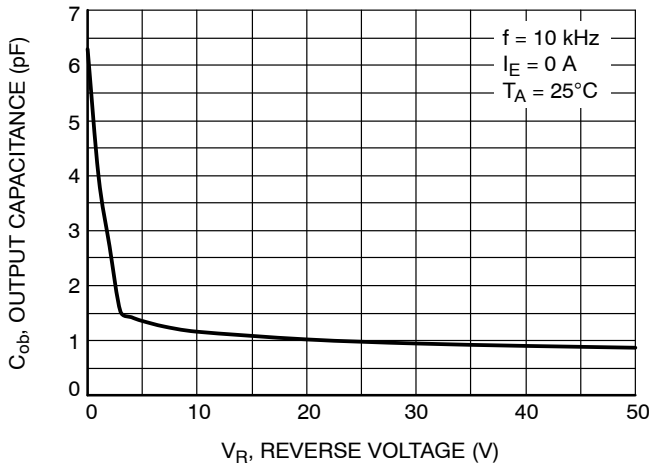


Figure 19. Output Capacitance

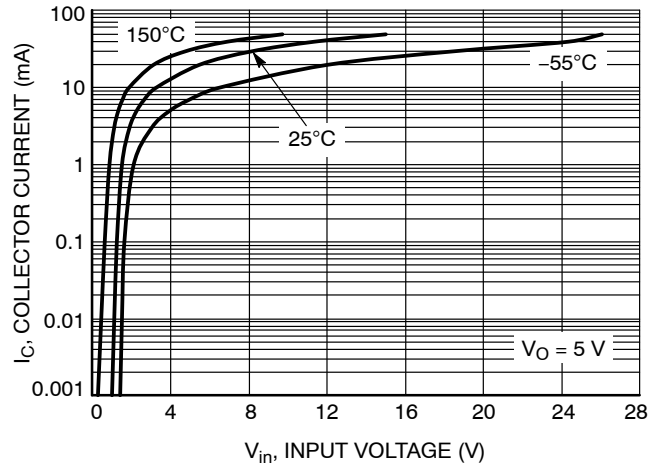


Figure 20. Output Current vs. Input Voltage

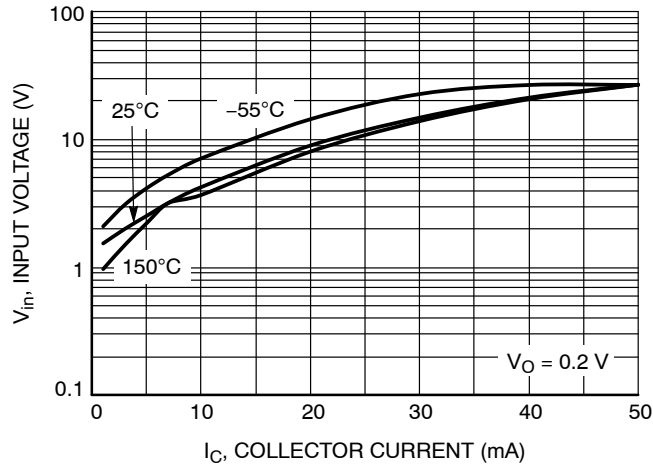


Figure 21. Input Voltage vs. Output Current

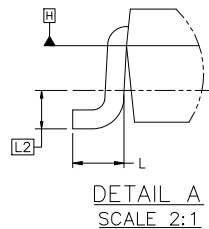
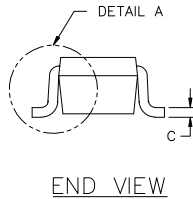
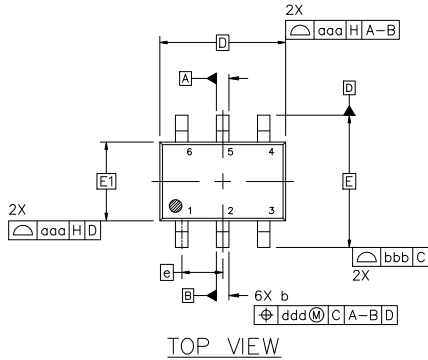


SC-88 2.00x1.25x0.90, 0.65P
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ISSUE Z

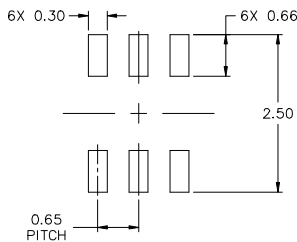
DATE 18 APR 2024

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

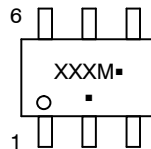


DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.10
A1	0.00	---	0.10
A2	0.70	0.90	1.00
b	0.15	0.20	0.25
c	0.08	0.15	0.22
D	2.00 BSC		
E	2.10 BSC		
E1	1.25 BSC		
e	0.65 BSC		
L	0.26	0.36	0.46
L2	0.15 BSC		
aaa	0.15		
bbb	0.30		
ccc	0.10		
ddd	0.10		



* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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CASE 419B-02
ISSUE Z

DATE 18 APR 2024

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13: PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 14: PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC	STYLE 15: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1	STYLE 16: PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1	STYLE 17: PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1	STYLE 18: PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1
STYLE 19: PIN 1. IOUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF	STYLE 20: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	STYLE 21: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1	STYLE 22: PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c)	STYLE 23: PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C	STYLE 24: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 25: PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1	STYLE 26: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 27: PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2	STYLE 28: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 29: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE	STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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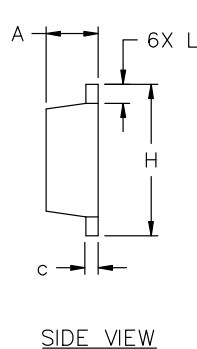
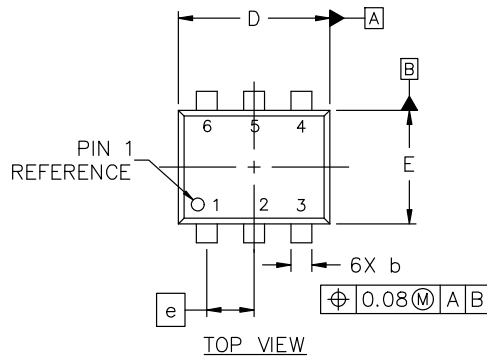


SOT-563-6 1.60x1.20x0.55, 0.50P
CASE 463A
ISSUE J

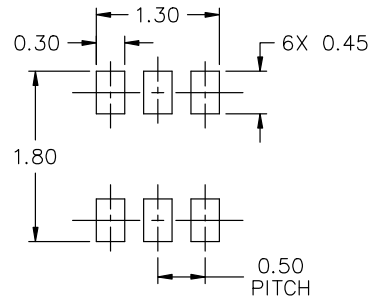
DATE 15 FEB 2024

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.50	0.55	0.60
b	0.17	0.22	0.27
c	0.08	0.13	0.18
D	1.50	1.60	1.70
E	1.10	1.20	1.30
e	0.50 BSC		
H	1.50	1.60	1.70
L	0.10	0.20	0.30



STYLE 1:
PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1

STYLE 2:
PIN 1. EMITTER 1
2. EMITTER 2
3. BASE 2
4. COLLECTOR 2
5. BASE 1
6. COLLECTOR 1

STYLE 3:
PIN 1. CATHODE 1
2. CATHODE 1
3. ANODE/ANODE 2
4. CATHODE 2
5. CATHODE 2
6. ANODE/ANODE 1

STYLE 4:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE
4. ANODE
5. CATHODE
6. CATHODE

STYLE 6:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE

STYLE 8:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

STYLE 9:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

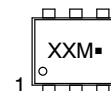
STYLE 10:
PIN 1. CATHODE 1
2. N/C
3. CATHODE 2
4. ANODE 2
5. N/C
6. ANODE 1

STYLE 11:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

GENERIC MARKING DIAGRAM*

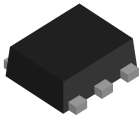


XX = Specific Device Code
M = Month Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	SOT-563-6 1.60x1.20x0.55, 0.50P	PAGE 1 OF 1

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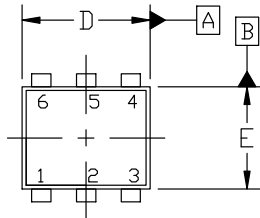


SOT-963 1.00x1.00x0.37, 0.35P
CASE 527AD
ISSUE F

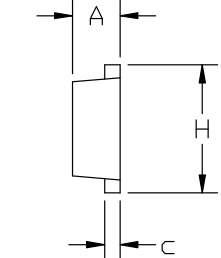
DATE 20 FEB 2024

NOTES:

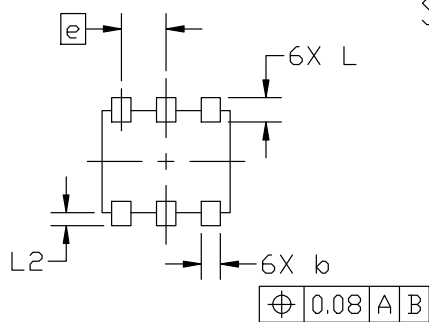
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.



TOP VIEW

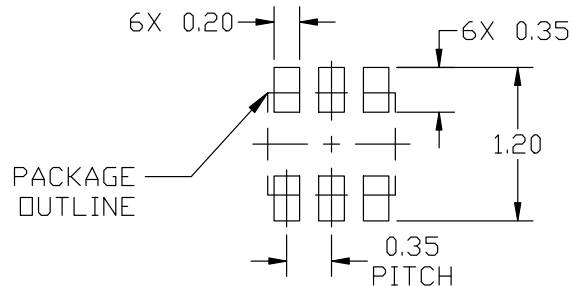


SIDE VIEW



BOTTOM VIEW

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.34	0.37	0.40
b	0.10	0.15	0.20
c	0.07	0.12	0.17
D	0.95	1.00	1.05
E	0.75	0.80	0.85
e	0.35 BSC		
H	0.95	1.00	1.05
L	0.19 REF		
L2	0.05	0.10	0.15

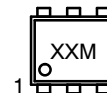


RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERRM/D.

- | | | |
|---|--|---|
| <p>STYLE 1:
PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1</p> | <p>STYLE 2:
PIN 1. EMITTER 1
2. EMITTER2
3. BASE 2
4. COLLECTOR 2
5. BASE 1
6. COLLECTOR 1</p> | <p>STYLE 3:
PIN 1. CATHODE 1
2. CATHODE 1
3. ANODE/ANODE 2
4. CATHODE 2
5. CATHODE 2
6. ANODE/ANODE 1</p> |
| <p>STYLE 4:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR</p> | <p>STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE
4. ANODE
5. CATHODE
6. CATHODE</p> | <p>STYLE 6:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE</p> |
| <p>STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE</p> | <p>STYLE 8:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN</p> | <p>STYLE 9:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1</p> |
| <p>STYLE 10:
PIN 1. CATHODE 1
2. N/C
3. CATHODE 2
4. ANODE 2
5. N/C
6. ANODE 1</p> | | |

GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Month Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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